

Photo DMOS-FET Relay

Description

The LT416 is a 1-Form A solid state relay in an 4 pin DIP package that employs optically coupled MOSFET technology to provide 3750V/5000V of input to output isolation. The optically coupled input is controlled by a highly efficient GaAlAs infrared LED and MOS FETs on the output side.

Features

- Low driver power requirements (TTL/CMOS Compatible)
- No moving parts
- High reliability
- Arc-Free with no snubbing circuits
- 3750 / 5000Vrms Input/Output isolation

Applications

- Telecommunications (PC, Electronic notepad)
- Measuring and Testing equipment
- Industrial control
- Security equipments
- High speed inspection machine

Outline Dimensions

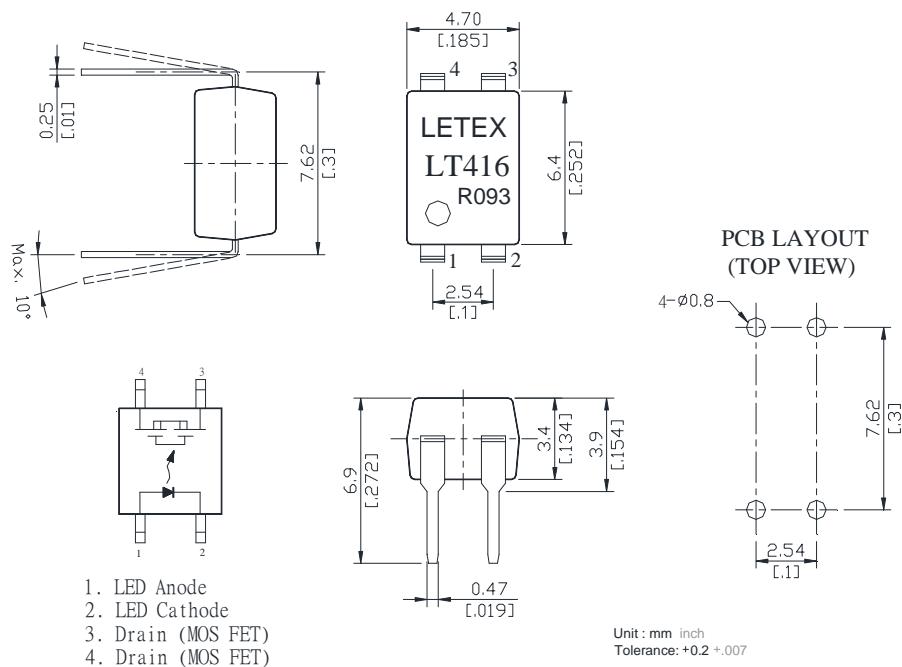


Photo DMOS-FET Relay Specifications

Part Name: LT416

(Load voltage:20V / Load current:2A)

Absolute Maximum Ratings (Ambient Temperature: 25°C)

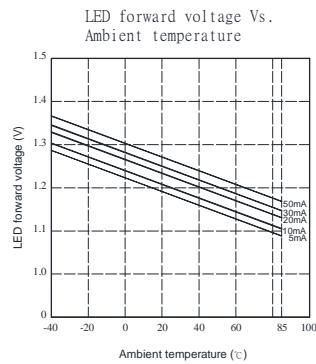
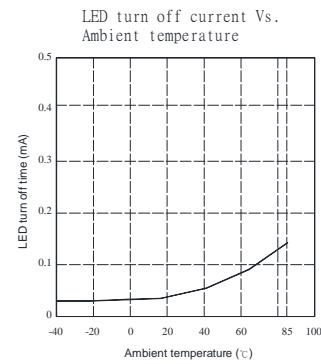
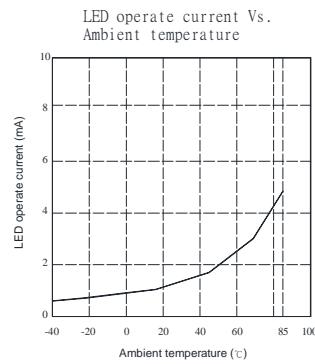
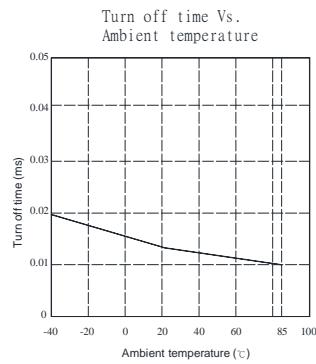
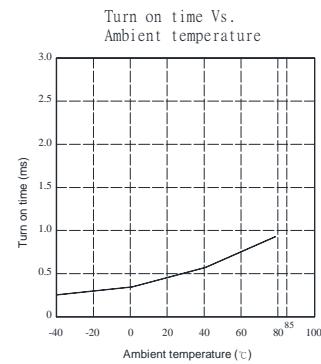
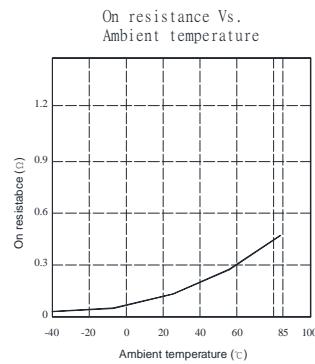
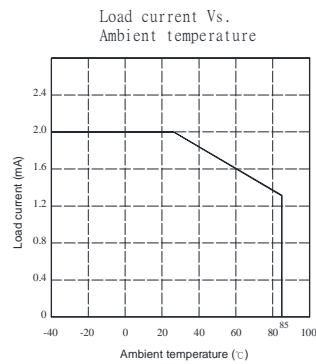
Item		Symbol	Value	Units	Note
Input	Continuous LED Current	I _F	50	mA	
	Peak LED Current	I _{FP}	1000	mA	f=100Hz, duty=1%
	LED Reverse Voltage	V _R	5	V	
	Input Power Dissipation	P _{In}	75	mW	
Output	Load Voltage	V _L	20	V(AC peak or DC)	
	Load Current	I _L	2	A	
	Peak Load Current	I _{Peak}	3.5	A	300 μs(1 pulse)
	Output Power Dissipation	P _{out}	450	mW	
Total Power Dissipation		P _T	500	mW	
I/O Breakdown Voltage		V _{I/O}	3750	Vrms	RH=60%, 1min
I/O Breakdown Voltage(Suffix-V)		V _{I/O}	5000	Vrms	RH=60%, 1min
Operating Temperature		T _{opr}	-40 to +85	°C	
Storage Temperature		T _{Stg}	-40 to +100	°C	
Pin Soldering Temperature		T _{Sol}	260	°C	10 sec max.

Electrical Specifications (Ambient Temperature: 25°C)

Item		Symbol	MIN.	TYP.	MAX.	Units	Conditions
Input	LED Forward Voltage	V _F		1.2	1.5	V	I _F =10mA
	Operation LED Current	I _{F On}		0.5	5.0	mA	
	Recovery LED Current	I _{F Off}		0.35	0.5	mA	
	Recovery LED Voltage	V _{F Off}	0.5			V	
Output	On-Resistance	R _{on}		0.1	0.5	Ω	I _F =10mA, I _L =100mA, Time to flow is within 1 sec.
	Off-State Leakage Current	I _{Leak}			1	μA	V _L =Rating
	Output Capacitance	C _{out}		150		pF	V _L =0, f=1MHz
Transmission	Turn-On Time	T _{on}		0.8	1.5	ms	I _F =10mA, I _L =100mA
	Turn-Off Time	T _{off}		0.02	0.5	ms	
Coupled	I/O Isolation Resistance	R _{I/O}	10 ¹⁰			Ω	DC500V
	I/O Capacitance	C _{I/O}		0.8	1.5	pF	f=1MHz



Reference Data



Voltage Vs. current characteristics
of output at MOS portion

